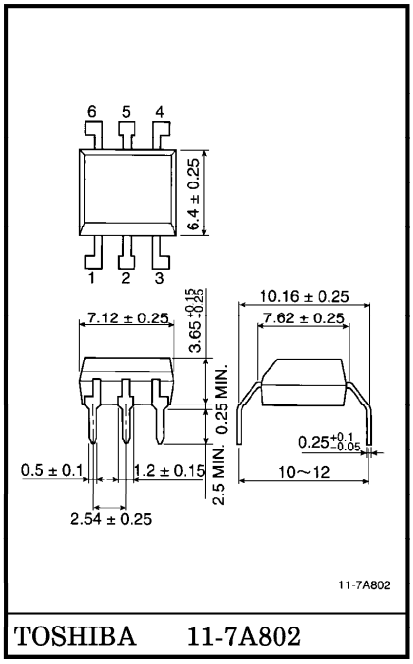
TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-TRANSISTOR

TLP733F, TLP734F

OFFICE MACHINE
SWITCHING POWER SUPPLY

Unit in mm



TOSHIBA 11-7A802

Weight : 0.42g

The TOSHIBA TLP733F and TLP734F consists of a photo-transistor optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP.
All parameters are tested to the specification of TLP733 and TLP734. (both condition and limits)

- Collector-Emitter Voltage : 55V (Min.)
- Current Transfer Ratio : 50% (Min.)
  Rank GB : 100% (Min.)
- UL Recognized : UL1577, File No.E67349
- BSI Approved : BS EN60065 : 1994
  Certificate No. 7364
  BS EN60950 : 1992
  Certificate No. 7365
- SEMKO Approved : SS4330784
  Certificate No.9325163, 9522142
- Isolation Voltage : 4000Vrms (Min.)
- Option (D4) type
  VDE Approved : DIN VDE0884 / 06.92,
  Certificate No. 74286, 91808

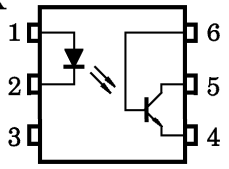
Maximum Operating Insulation Voltage : 890, 1130V_{PK}
Highest Permissible Over Voltage : 6000, 8000V_{PK}

(Note) When a VDE0884 approved type is needed, please designate the "Option (D4)"

- Creepage Distance : 8.0mm (Min.)
  Clearance : 8.0mm (Min.)
  Internal Creepage Path : 4.0mm (Min.)
  Insulation Thickness : 0.5mm (Min.)
- Conforming Safety Standards :
  DIN 57 804.VDE0804 / 1.83
  DIN IEC65 / VDE0860 / 8.81
  DIN IEC380 / VDE0806 / 8.81
  DIN IEC435 / VDE0805 / Draft Nov.84
  DIN IEC601T1 / VDE0750T1 / 5.82
  BS7002 : 1989 (EN60950)

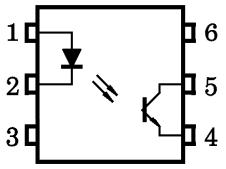
PIN CONFIGURATIONS (TOP VIEW)

TLP733



1 : ANODE
2 : CATHODE
3 : NC
4 : EMITTER
5 : COLLECTOR
6 : BASE

TLP734



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